

## Supplementary Materials

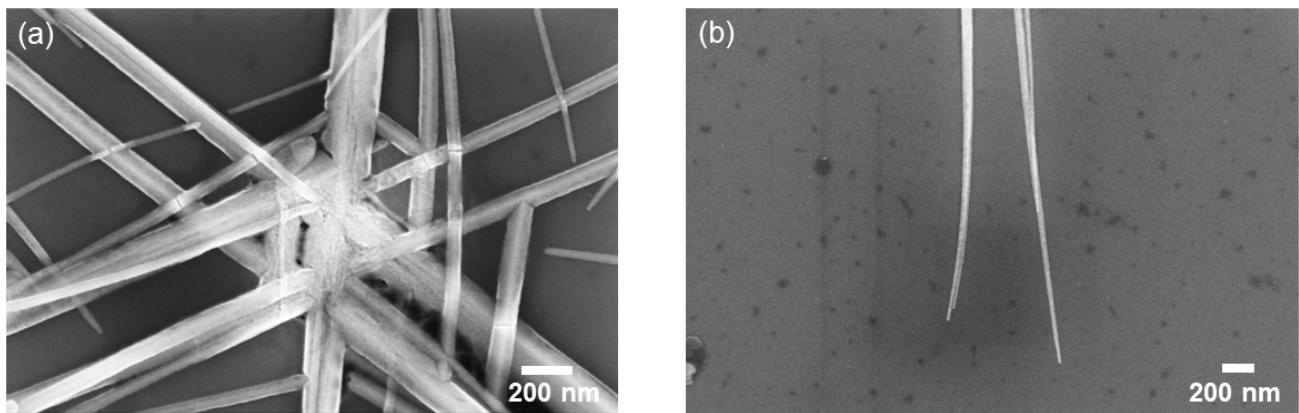
# Low-Cost, High-Yield ZnO Nanostars Synthesis for Pseudocapacitor Applications

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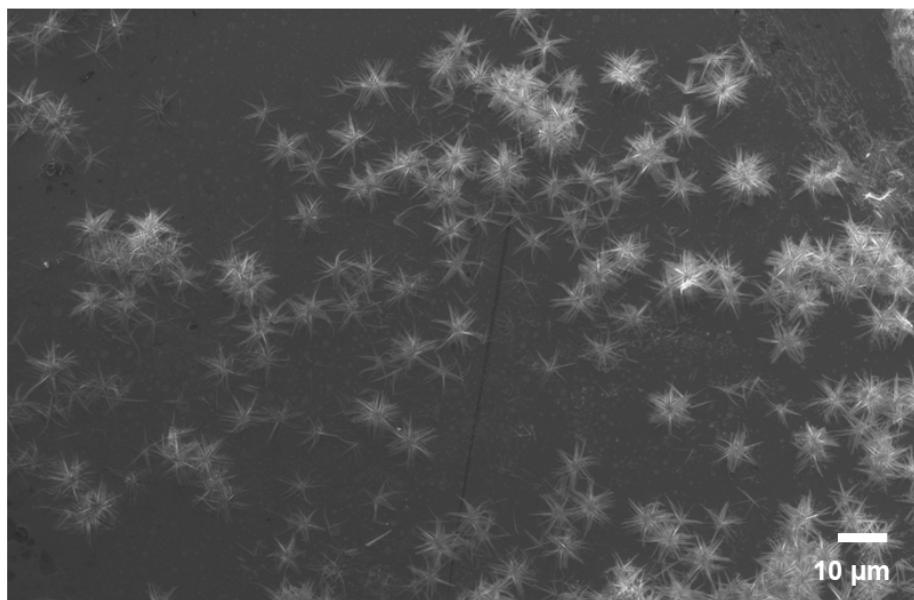
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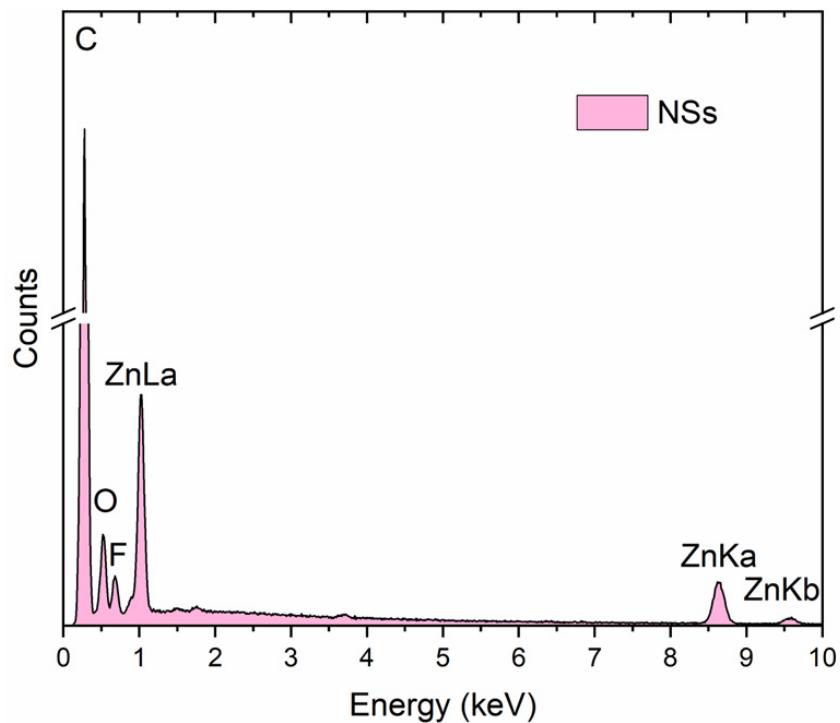
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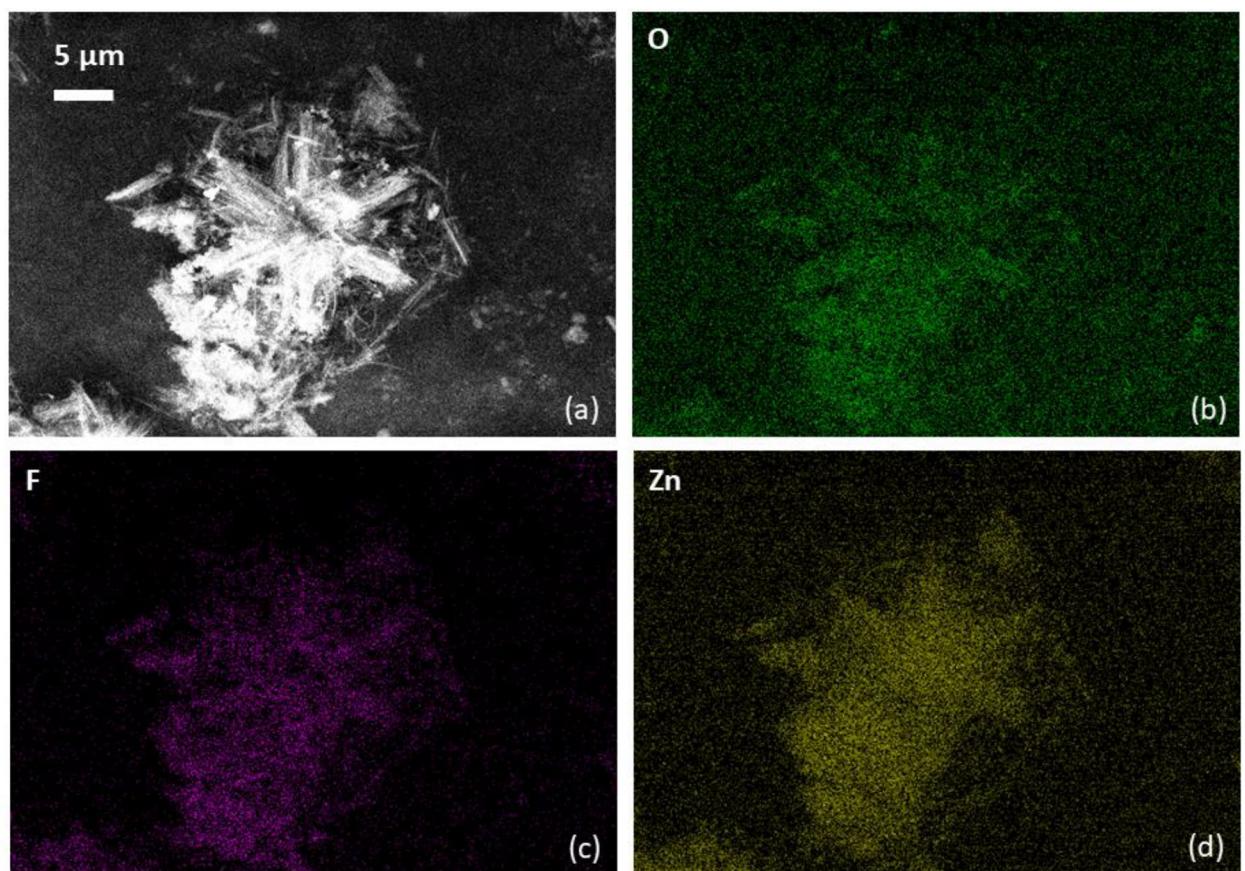
**Figure S1.** (a) High magnification SEM of an NS center and (b) an NS tip.



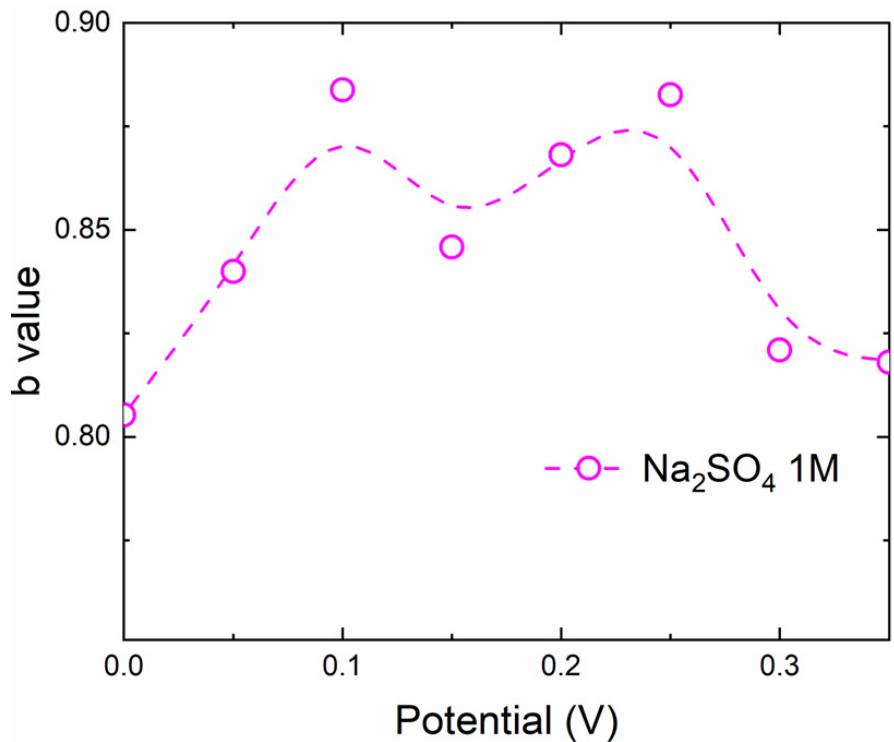
**Figure S2.** SEM image of AnnNSs.



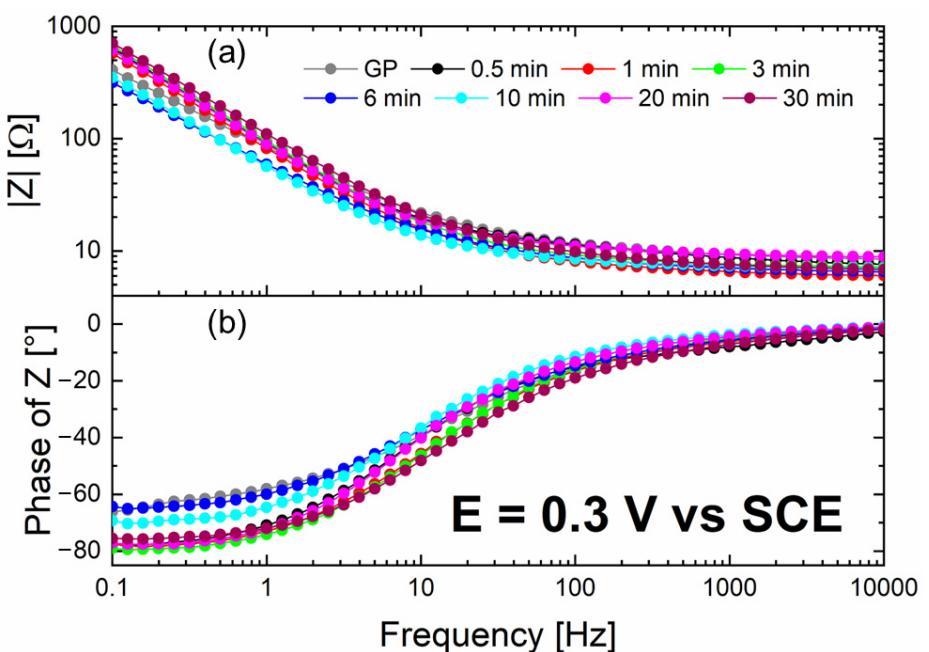
**Figure S3.** EDX spectrum taken in NSs grown for 10 min.



**Figure S4.** SEM micrograph of (a) single grown NS and (b-d) related SEM-EDX mapping for O, F and Zn elements respectively. EDX maps were acquired setting the operating voltage as 20 kV and a working distance of 8.5 mm.



**Figure S5.** Extrapolated b values for 10 min NSs in 1 M  $\text{Na}_2\text{SO}_4$  at different scan rates as a function of potential values.



**Figure S6.** Bode Plot from the EIS analyses acquired at 0.3 V: (a) impedance modulus and (b) phase angle amplitudes for all growth times analyzed. Data for the GP substrate are also reported (GP grey, 0.5 min black, 1 min red, 3 min green, 6 min blue, 10 min light blue, 20 min magenta, and 30 min Bordeaux lines and circles).